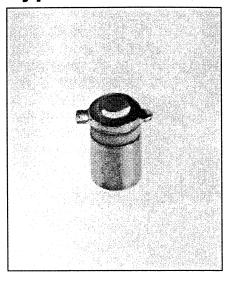
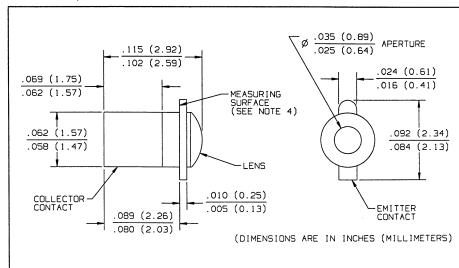


NPN Silicon Phototransistors Types OP600A, OP600B, OP600C





Features

- · Narrow receiving angle
- Variety of sensitivity ranges
- Enhanced temperature range
- · Ideal for direct mounting in PC boards
- Mechanically and spectrally matched to the OP123 and OP223 series devices
- TX/TXV processing available (see Hi-Rel section)

Description

The OP600 series device consists of an NPN silicon phototransistor mounted in a hermetically sealed "Pill" type package. The narrow receiving angle provides excellent on-axis coupling. These devices are 100% production tested using infrared light for close correlation with Optek GaAs and GaAlAs emitters.

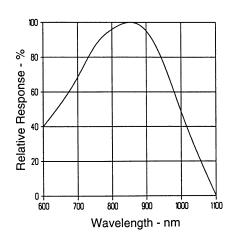
Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

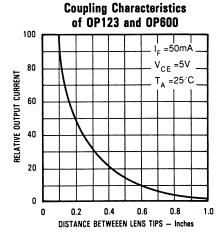
Collector-Emitter Voltage
Emitter-Collector Voltage 5.0 V
Storage Temperature Range
Operating Temperature Range65° C to +125° C
Soldering Temperature (5 sec. with soldering iron)
Power Dissipation
Continuous Collector Current 50 mA
Notes:

- (1) Refer to Application Bulletin 202 which discusses proper techniques for soldering Pill type devices to PC boards.
- (2) No clean or low solids, RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (3) Derate linearly 0.5mW/° C above 25° C.
- (4) Junction temperature maintained at 25° C.
- (5) Light source is a GaAlAs LED, peak Wavelength = 890 nm, providing an irradiance of 2.5 mW/cm². The source irradiance is not necessarily uniform over the entire lens area of the unit under test.

Typical Performance Curves

Typical Spectral Response



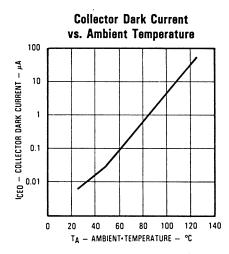


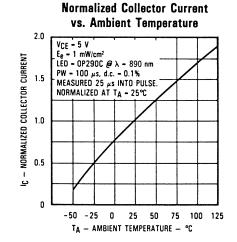
Types OP600A, OP600B, OP600C

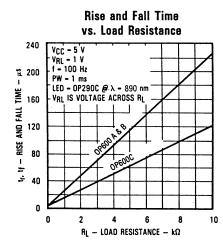
Electrical Characteristics (T_A = 25° C unless otherwise noted)

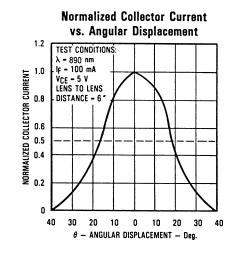
SYMBOL	PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITIONS
I _{C(ON)} ⁽⁴⁾	On-State Collector Current	OP600C OP600B OP600A	0.30 0.60 1.20		1.8	mA mA mA	$V_{CE} = 5 \text{ V, } E_e = 2.5 \text{ mW/cm}^{2(5)}$
ICEO	Collector Dark Current					nA	V _{CE} = 10 V, E _e = 0
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage		25			٧	I _C = 100 μA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage		5.0			٧	I _E = 100 μA
VCE(SAT) ⁽⁴⁾	Collector-Emitter Saturation Voltage				0.40	٧	$I_C = 0.15 \text{ mA}, E_e = 2.5 \text{ mW/cm}^{2(5)}$
	Rise Time Fall Time			15 15		μs μs	V_{CC} = 5 V, I_C = 0.80 mA, R_L = 1 k Ω , See Test Circuit

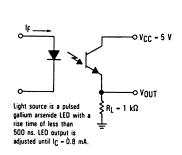
Typical Performance Curves











Switching Time

Test Circuit

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ADPD2214ACPZ-R7 SD5600-001 SD5610-001 SD5630-001 SD5630-002 SDP8304-301 SDP8600-003 SDP8601-001 SDP8601-002
SDP8610-003 SDP8611-001 SDP8611-002 SDP8611-003 SDP8614-301 LTDL-TA16A QSE159 QSE259 OP572 OPB892N55Z
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OPL530-OC OPL531A